

# FH8810K6

## N- Channel Enhancement Mode Power MOSFET

### Description

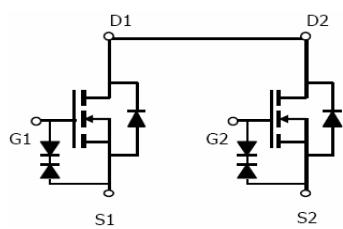
The FH8810K6 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

### Application

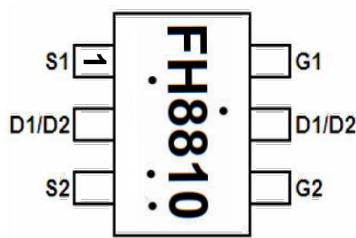
- Uni-directional load switch
- Bi-directional load switch

### General Features

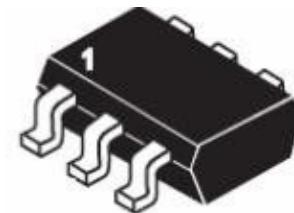
- $V_{DS} = 20V$ ,  $I_D = 7A$
- $R_{DS(ON)} < 14.5 \text{ m}\Omega$  (Typ) @  $V_{GS}=4.5V$
- $R_{DS(ON)} < 15.5 \text{ m}\Omega$  (Typ) @  $V_{GS}=3.7V$
- $R_{DS(ON)} < 17 \text{ m}\Omega$  (Typ) @  $V_{GS}=3.1V$
- $R_{DS(ON)} < 19 \text{ m}\Omega$  (Typ) @  $V_{GS}=2.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package
- ESD Rating: 2000V HBM



Schematic diagram



Marking and pin Assignment



SOT23-6 top view

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain Source Voltage	$V_{DS}$	20	V
Gate Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current Continuous	$I_D$	7	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	28	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	98	°C/W
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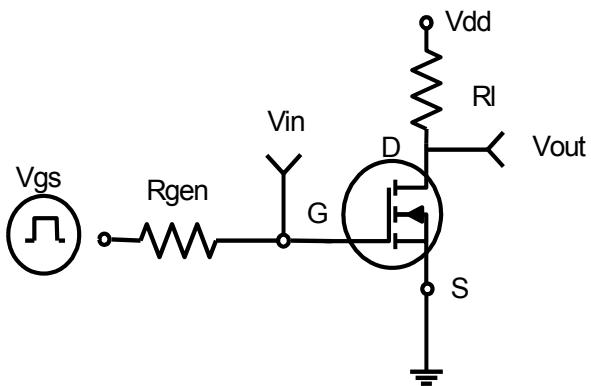
**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=18\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS1}}$	$V_{\text{GS}}= \pm 8\text{ V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 1$	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS2}}$	$V_{\text{GS}}= \pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=4.5\text{A}$		14.5	17	$\text{m}\Omega$
		$V_{\text{GS}}=3.7\text{V}, I_{\text{D}}=4\text{A}$	-	15.5	18.5	$\text{m}\Omega$
		$V_{\text{GS}}=3.1\text{V}, I_{\text{D}}=4\text{A}$	-	17	20.5	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=2\text{A}$	-	19	23.5	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=6\text{A}$	-	35	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$		993		PF
Output Capacitance	$C_{\text{oss}}$		-	210	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$			139		PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=10\text{V}, R_{\text{L}}=1.2\Omega$ $V_{\text{GS}}=8\text{V}, R_{\text{GEN}}=3\Omega$	-	2.5		nS
Turn-on Rise Time	$t_r$		-	7.2		nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	49		nS
Turn Off Fall Time	$t_f$		-	10.8		nS
Total Gate Charge	$Q_g$	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=6\text{A}, V_{\text{GS}}=4.5\text{V}$	-	14.2		nC
Gate-Source Charge	$Q_{\text{gs}}$		-	1.5	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	4.7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=1\text{A}$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_{\text{s}}$		-	-	7	A

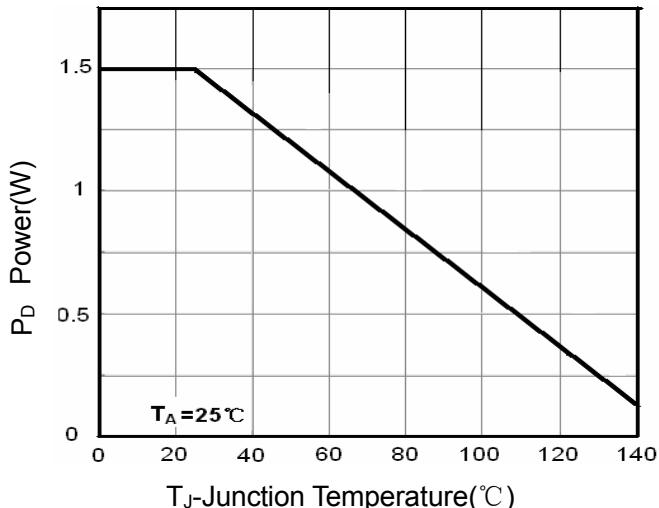
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10\text{ sec}$ .
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

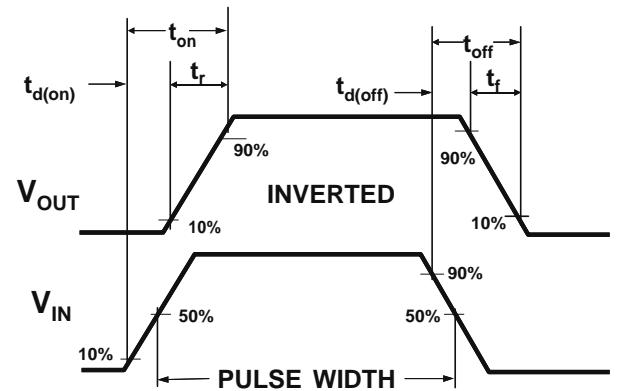
### Typical Electrical and Thermal Characteristics



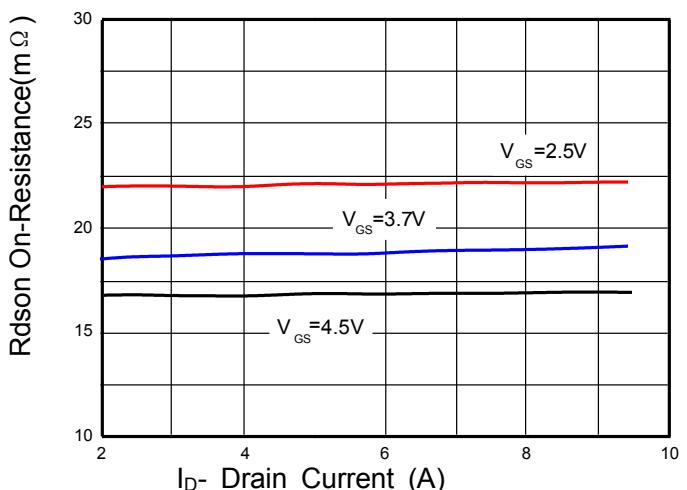
**Figure 1:Switching Test Circuit**



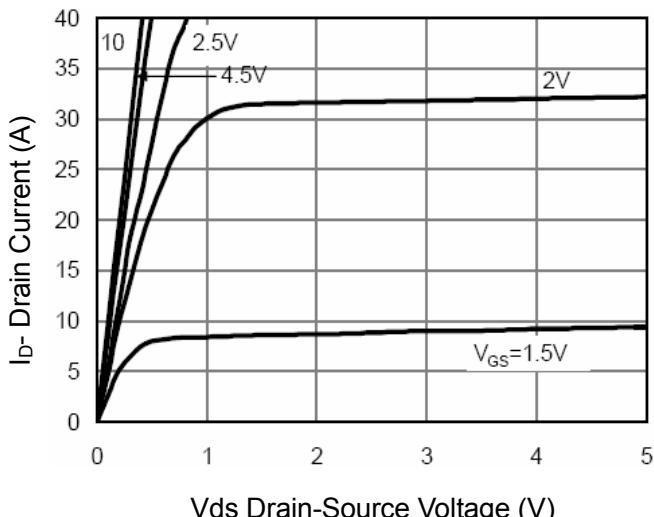
**Figure 3 Power Dissipation**



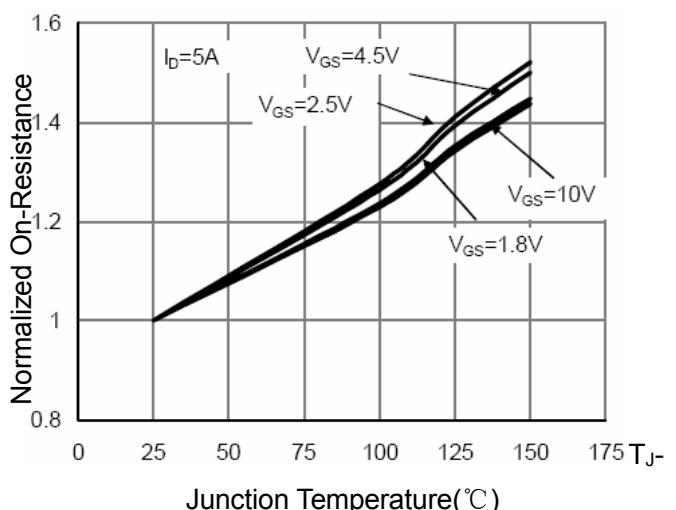
**Figure 2:Switching Waveforms**



**Figure 6 Drain-Source On-Resistance**



**Figure 5 Output Characteristics**



**Figure 8 Drain-Source On-Resistance**

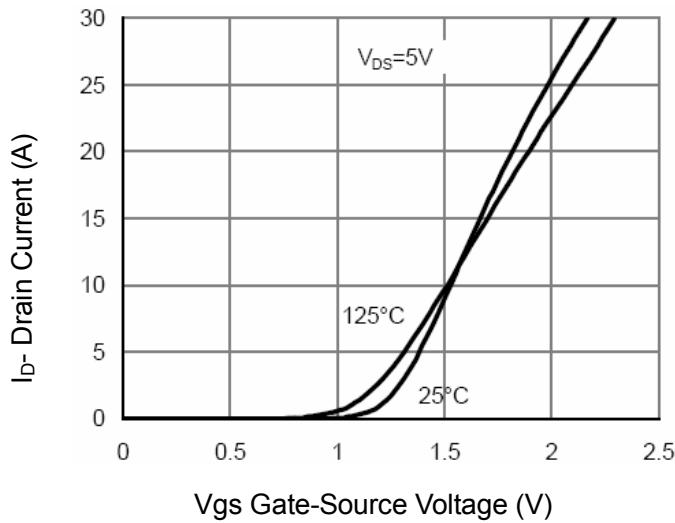


Figure 7 Transfer Characteristics

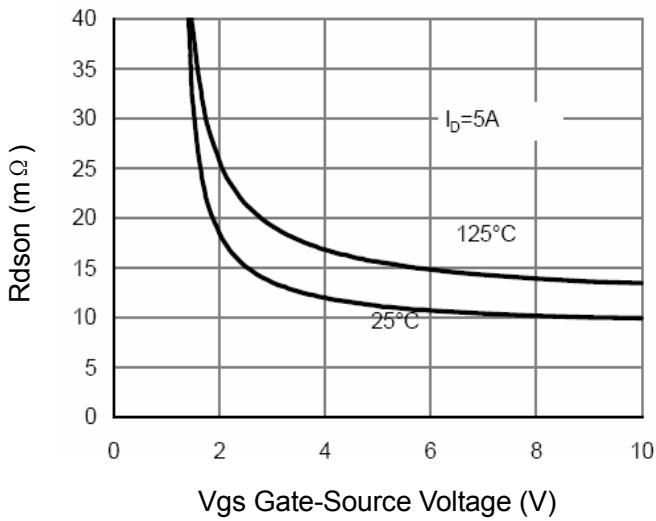


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

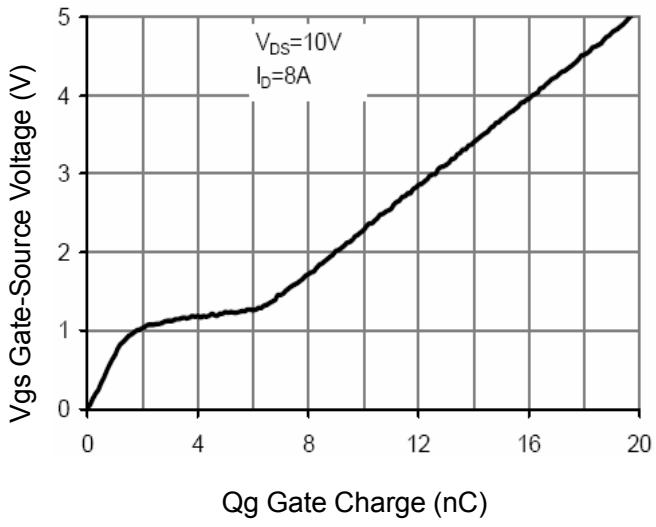


Figure 11 Gate Charge

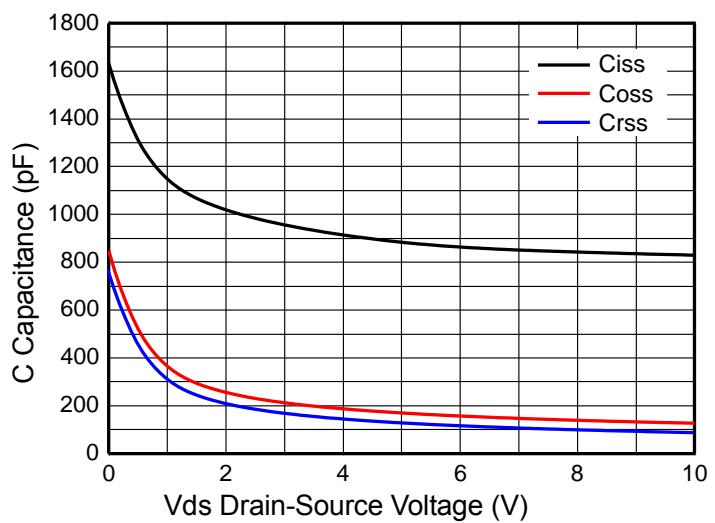


Figure 8 Capacitance vs  $V_{DS}$

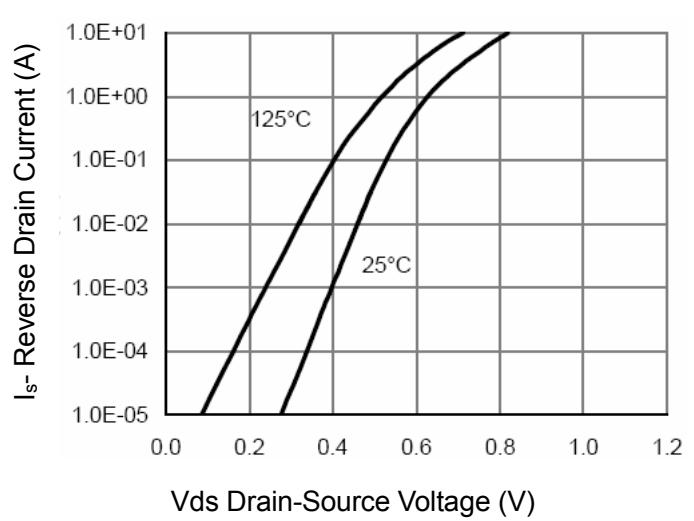


Figure 10 Capacitance vs  $V_{DS}$

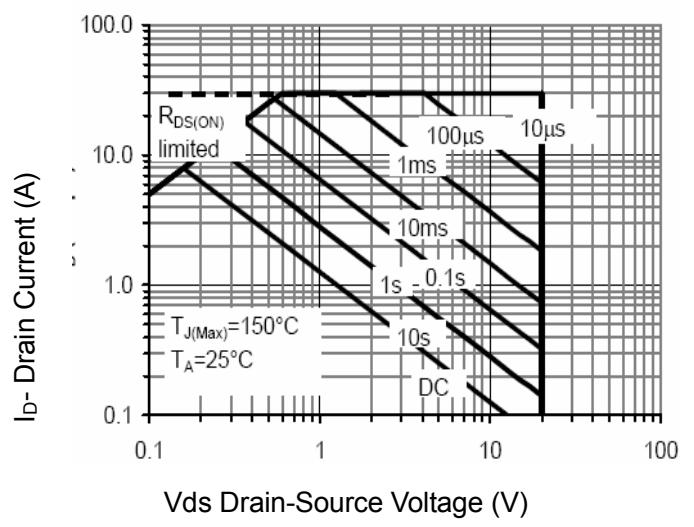


Figure 13 Safe Operation Area

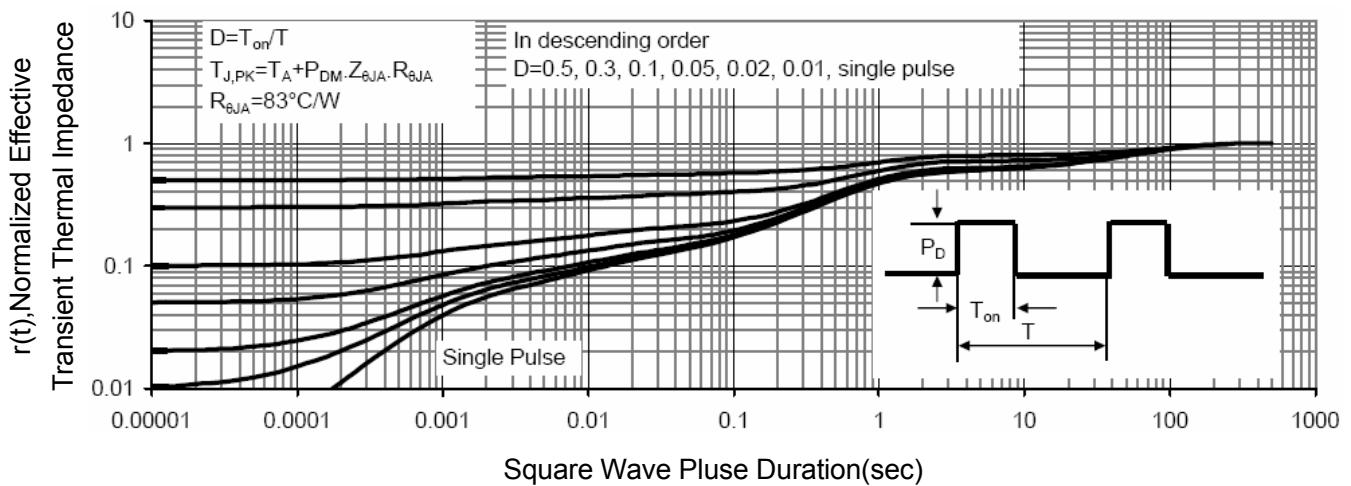
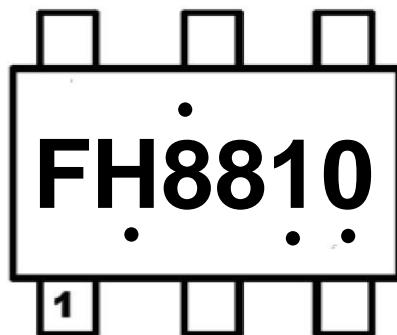


Figure 14 Normalized Maximum Transient Thermal Impedance

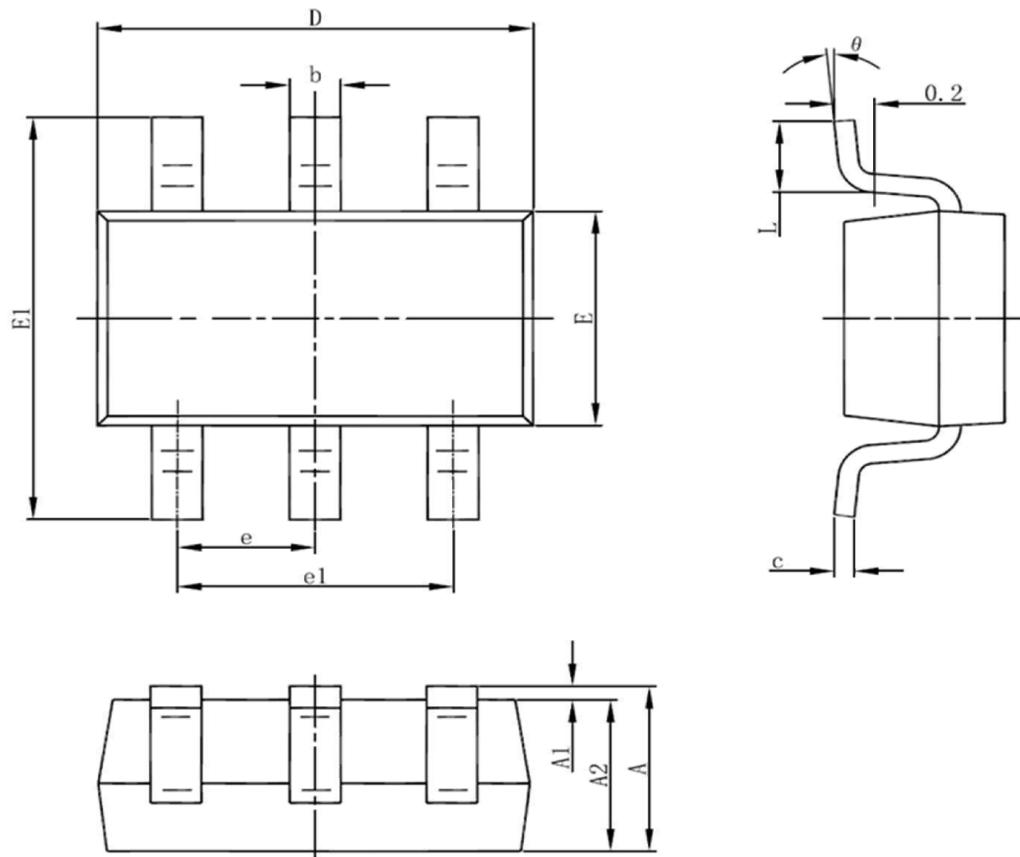
MARKING DESCRIPTION

SOT23-6



**Note:**

- 1、 MARK: FH8810 is the product model of FH8810K6
- 2、 The printing points above and below the product model are the internal identification of the company. Each batch of products may be in different locations.

**Package Information : SOT23-6**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.750	3.150	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.500	3.100	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°